

Listing of Claims and Amendments thereto:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of producing an acoustic resonator device, comprising:

depositing a first metal film on a substrate;

patterning said first metal film;

depositing piezoelectric material on said first metal film;

depositing a second metal film on said piezoelectric material;

patterning said second metal film ~~to form a complete acoustic resonator device~~; and

removing some or all piezoelectric material not involved in signal transmission ~~after said acoustic resonator device is formed~~ by a selective etching process to limit lateral propagation losses to un-etched regions of the ~~formed~~ acoustic resonator device, said removing step performed after said second metal film is patterned.

2-9 (Canceled)

10. (Original) The method of claim 1, wherein said piezoelectric material is selected from the group comprising at least AlN, ZnO and CdS.

11. (Previously Presented) The method of claim 1, wherein said first and second metal films are formed by lithographic patterning of Al metal or other conductors.

12. (Previously Presented) The method of claim 1, wherein said substrate is formed as a plurality of acoustic reflecting layers on a substrate such as a silicon, quartz, or glass wafer.

13. (Currently Amended) A method of isolating an acoustic resonator device, comprising:

depositing a first metal film on a substrate;
depositing piezoelectric material on said first metal film;
depositing a second metal film on said piezoelectric material ~~to form a complete acoustic resonator device;~~
and
removing some or all piezoelectric material not involved in signal transmission with a selective etching process ~~that is performed after said acoustic resonator device is formed,~~ to limit propagation of energy in lateral modes, said removing step performed after said second metal film is deposited on said piezoelectric material.

14. (Canceled)

15. (Previously Presented) The method of claim 13, wherein at least some of the substrate surface is removed by selective etching.

16. (Original) The method of claim 13, wherein at least some of the removed piezoelectric material forms a void which is back filled with a different material.

17-28 (Canceled)

29. (Previously Presented) The method of claim 1, wherein said deposited piezoelectric material is deposited as a continuous layer on said first metal film.

30. (Previously Presented) The method of claim 29, wherein the continuous piezoelectric layer is not patterned.

31. (Previously Presented) The method of claim 13, wherein said deposited piezoelectric material is deposited as a continuous layer on said first metal film.

32. (Previously Presented) The method of claim 31, wherein the continuous piezoelectric layer is not patterned.
